

# Radar Pulsed Power Transistor, 65W, 100μs Pulse, 10% Duty 2.7 - 2.9 GHz

## PH2729-65M

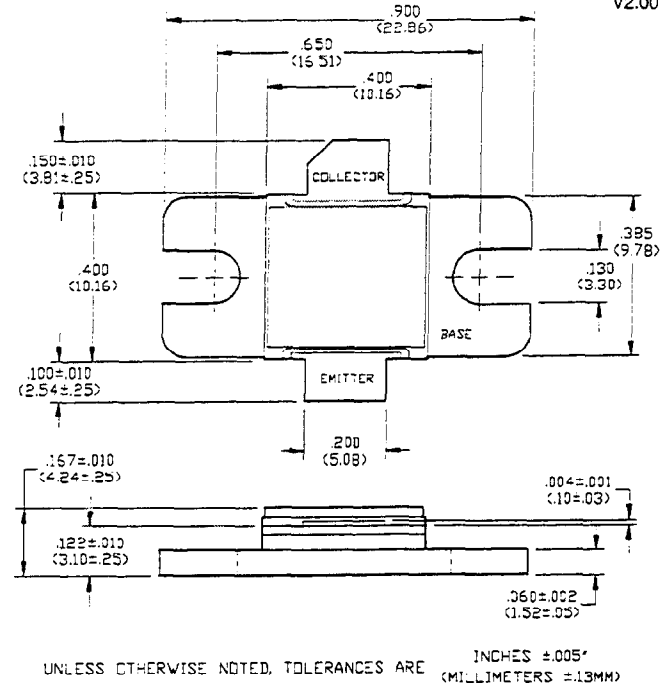
V2.00

### Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

### Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	65	V
Emitter-Base Voltage	$V_{EB0}$	3.0	V
Collector Current (Peak)	$I_C$	8.0	A
Total Power Dissipation	$P_{TOT}$	330	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-65 to +200	°C

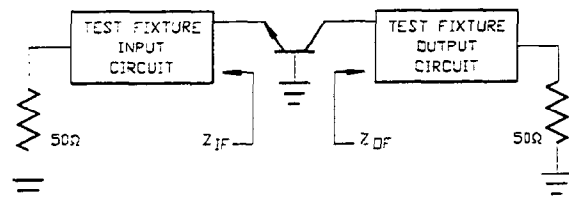


### Electrical Characteristics at 25°C

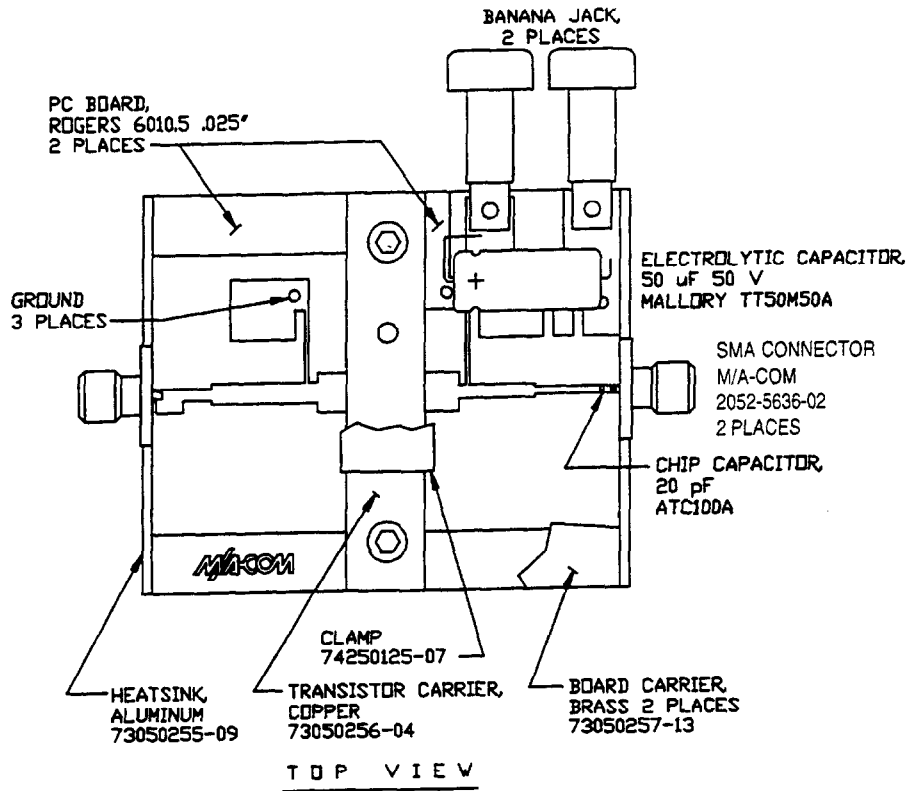
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	$BV_{CES}$	65	-	V	$I_C=50$ mA
Collector-Emitter Leakage Current	$I_{CES}$	-	7.5	mA	$V_{CE}=36$ V
Thermal Resistance	$R_{TH(JC)}$	-	0.45	°C/W	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Input Power	$P_{IN}$	-	9.0	W	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Power Gain	$G_P$	8.5	-	dB	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Collector Efficiency	$\eta_C$	40	-	%	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Input Return Loss	RL	9	-	dB	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Load Mismatch Tolerance	VSWR-T	-	2:1	-	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz
Load Mismatch Stability	VSWR-S	-	1.5:1	-	$V_{CC}=36$ V, $P_{OUT}=65$ W, $F=2.7, 2.8, 2.9$ GHz

### Broadband Test Fixture Impedances

F(GHz)	$Z_{IF}(\Omega)$	$Z_{OF}(\Omega)$
2.70	7.8 - j8.3	9.3 - j8.9
2.80	7.3 - j6.7	9.0 - j8.4
2.90	7.2 - j5.0	8.6 - j8.0



RF Test Fixture



Test Fixture PC Board Dimensions

